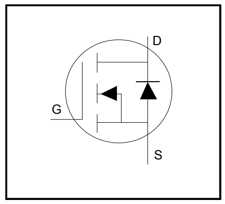
International
IOR Rectifier

StrongIRFET™ IRFR7746PbF IRFU7746PbF

HEXFET® Power MOSFET

Application

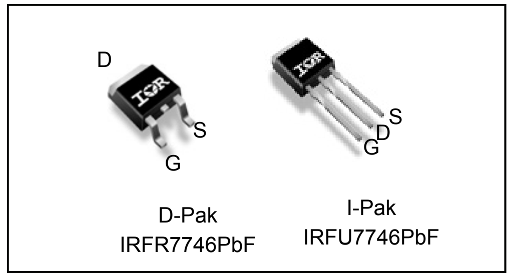
- Brushed Motor drive applications
- BLDC Motor drive applications
- Battery powered circuits
- Half-bridge and full-bridge topologies
- Synchronous rectifier applications
- Resonant mode power supplies
- OR-ing and redundant power switches
- DC/DC and AC/DC converters
- DC/AC Inverters



V_{DSS}	75V
$R_{DS(on)}$ typ.	9.5mΩ
max	11.2mΩ
I_D (Silicon Limited)	59A①
I_D (Package Limited)	56A

Benefits

- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche SOA
- Enhanced body diode dV/dt and dI/dt Capability
- Lead-Free, RoHS Compliant



G	D	S
Gate	Drain	Source

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRFR7746PbF	D-Pak	Tube	75	IRFR7746PbF
		Tape and Reel	2000	IRFR7746TRPbF
IRFU7746PbF	I-Pak	Tube	75	IRFU7746PbF

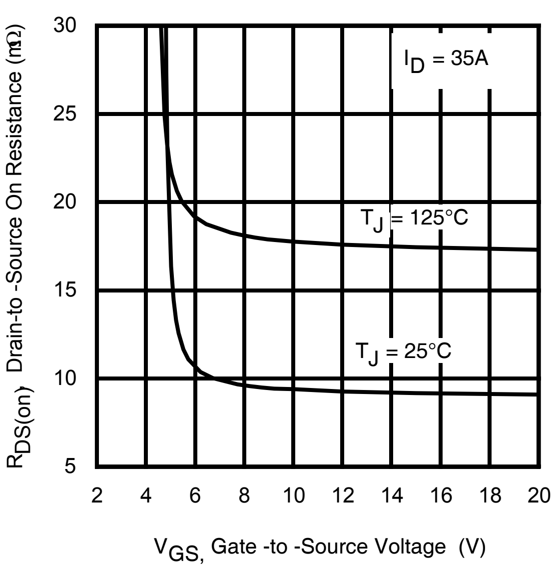


Fig 1. Typical On-Resistance vs. Gate Voltage

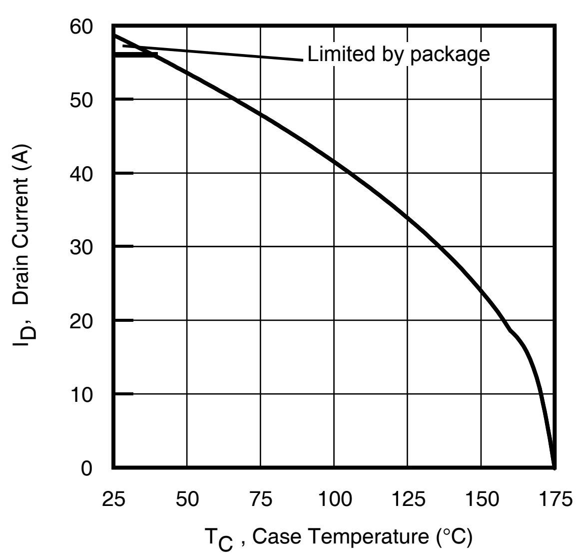


Fig 2. Maximum Drain Current vs. Case Temperature

Absolute Maximum Rating

Symbol	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V (Silicon Limited)	59①	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V (Silicon Limited)	42	
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V (Wire Bond Limited)	56	
I_{DM}	Pulsed Drain Current ②	230*	
P_D @T_C = 25°C	Maximum Power Dissipation	99	W
	Linear Derating Factor	0.66	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	

Avalanche Characteristics

$E_{AS\ (Thermally\ limited)}$	Single Pulse Avalanche Energy ③	116	mJ
$E_{AS\ (Thermally\ limited)}$	Single Pulse Avalanche Energy ⑩	160	
I_{AR}	Avalanche Current ②	See Fig 15, 16, 23a, 23b	A
E_{AR}	Repetitive Avalanche Energy ②		mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑧	——	1.52	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ⑨	——	50	
$R_{\theta JA}$	Junction-to-Ambient	——	110	

Static @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	75	——	——	V	V_{GS} = 0V, I_D = 250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	——	53	——	mV/°C	Reference to 25°C, I_D = 1mA ②
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	——	9.5	11.2	mΩ	V_{GS} = 10V, I_D = 35A
		——	11.2	——		V_{GS} = 6.0V, I_D = 18A
$V_{GS(th)}$	Gate Threshold Voltage	2.1	——	3.7	V	V_{DS} = V_{GS}, I_D = 100μA
I_{DSS}	Drain-to-Source Leakage Current	——	——	1.0	μA	V_{DS} =75 V, V_{GS} = 0V
		——	——	150		V_{DS} =75V,V_{GS} = 0V,T_J =125°C
I_{GSS}	Gate-to-Source Forward Leakage	——	——	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	——	——	-100		V_{GS} = -20V
R_G	Gate Resistance	——	1.6	——	Ω	

Notes:

① Calculated continuous current based on maximum allowable junction temperature. Bond wire current limit is 56A by source bonding technology. Note that current limitations arising from heating of the device leads may occur with some lead mounting arrangements. (Refer to AN-1140)

② Repetitive rating; pulse width limited by max. junction temperature.

③ Limited by T_{Jmax}, starting T_J = 25°C, L = 190μH, R_G = 50Ω, I_{AS} = 35A, V_{GS} =10V.

④ $I_{SD} \leq$ 35A, di/dt ≤ 570A/μs, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq$ 175°C.

⑤ Pulse width ≤ 400μs; duty cycle ≤ 2%.

⑥ C_{oss} eff. (TR) is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

⑦ C_{oss} eff. (ER) is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

⑧ R_θ is measured at T_J approximately 90°C.

⑨ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.please refer to application note to AN-994: http://www.irf.com/technical-info/appnotes/an-994.pdf

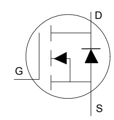
⑩ Limited by T_{Jmax}, starting T_J = 25°C, L = 1mH, R_G = 50Ω, I_{AS} = 18A, V_{GS} =10V

* Pulse drain current is limited at 224A by source bonding technology.

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
gfs	Forward Transconductance	112	——	——	S	V_{DS} = 10V, I_D =35A
Q_g	Total Gate Charge	——	59	89	nC	I_D = 35A
Q_{gs}	Gate-to-Source Charge	——	14	——		V_{DS} = 38V
Q_{gd}	Gate-to-Drain Charge	——	18	——		V_{GS} = 10V
Q_{sync}	Total Gate Charge Sync. (Qg– Qgd)	——	41	——		
$t_{d(on)}$	Turn-On Delay Time	——	7.9	——	ns	V_{DD} = 38V
t_r	Rise Time	——	30	——		I_D = 35A
$t_{d(off)}$	Turn-Off Delay Time	——	34	——		R_G= 2.7Ω
t_f	Fall Time	——	21	——		V_{GS} = 10V⑤
C_{iss}	Input Capacitance	——	3107	——	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	——	257	——		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	——	159	——		*ƒ* = 1.0MHz, See Fig.7
$C_{oss\ eff.(ER)}$	Effective Output Capacitance (Energy Related)	——	234	——		V_{GS} = 0V, VDS = 0V to 60V⑦
$C_{oss\ eff.(TR)}$	Output Capacitance (Time Related)	——	299	——		V_{GS} = 0V, VDS = 0V to 60V⑥

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	——	——	59①	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ②	——	——	230*		
V_{SD}	Diode Forward Voltage	——	——	1.2	V	T_J = 25°C,I_S = 35A,V_{GS} = 0V ⑤
dv/dt	Peak Diode Recovery dv/dt④	——	8.1	——	V/ns	T_J = 175°C,I_S = 35A,V_{DS} = 75V
t_{rr}	Reverse Recovery Time	——	27	——	ns	T_J = 25°C V_{DD} = 64V
		——	32	——		T_J = 125°C I_F = 35A,
Q_{rr}	Reverse Recovery Charge	——	26	——	nC	T_J = 25°C di/dt = 100A/μs ⑤
		——	36	——		T_J = 125°C
I_{RRM}	Reverse Recovery Current	——	1.7	——	A	T_J = 25°C

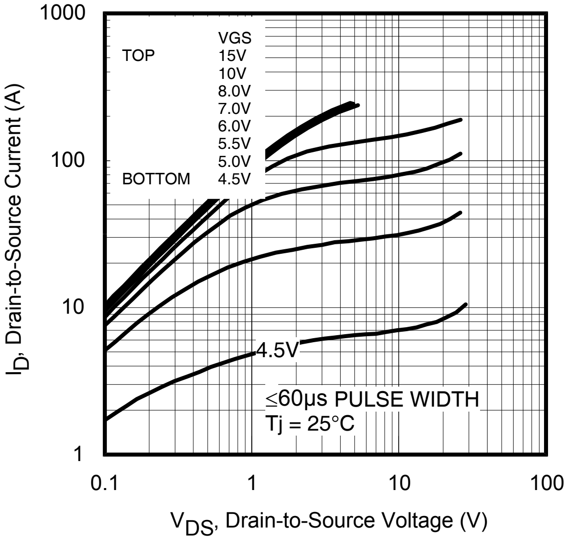


Fig 3. Typical Output Characteristics

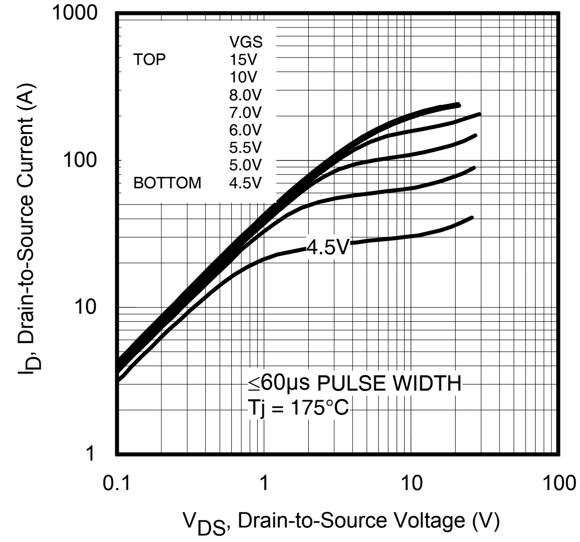


Fig 4. Typical Output Characteristics

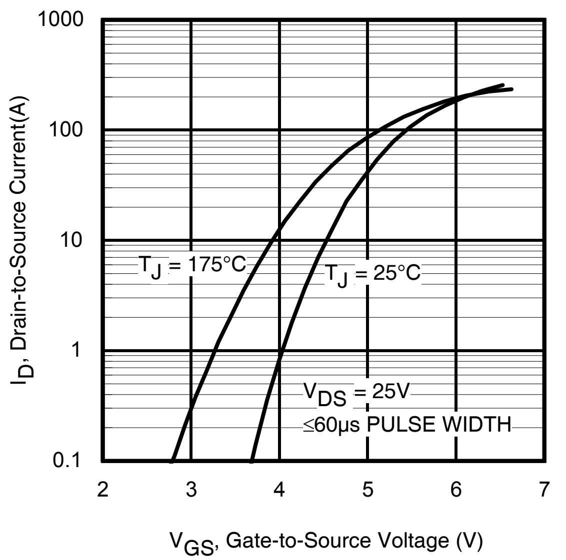


Fig 5. Typical Transfer Characteristics

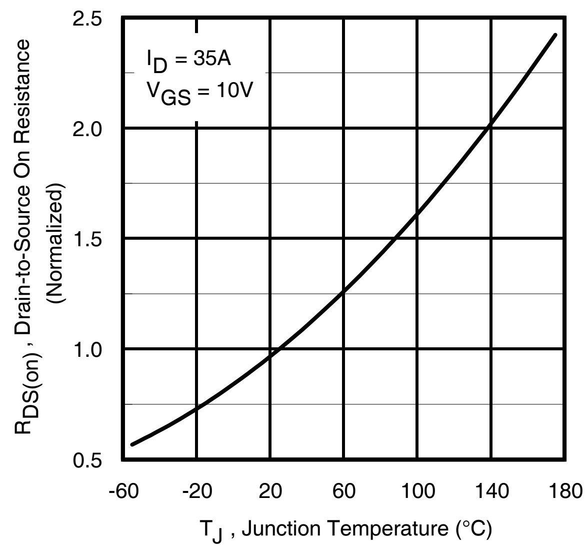


Fig 6. Normalized On-Resistance vs. Temperature

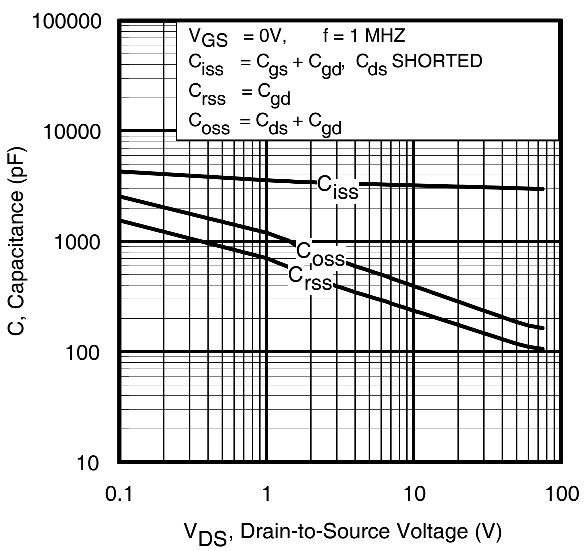


Fig 7. Typical Capacitance vs. Drain-to-Source Voltage

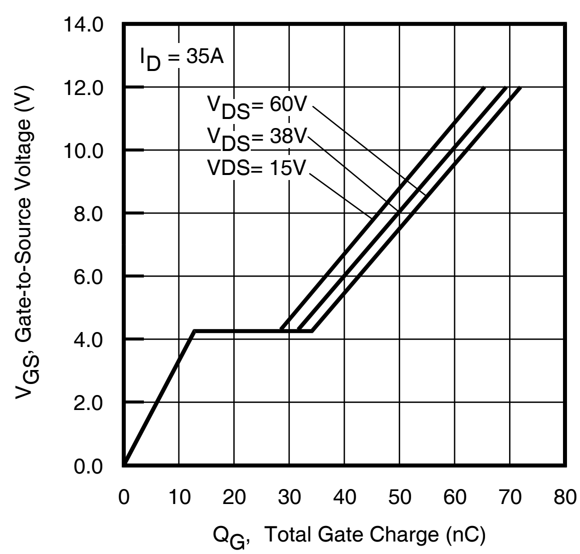


Fig 8. Typical Gate Charge vs. Gate-to-Source Voltage

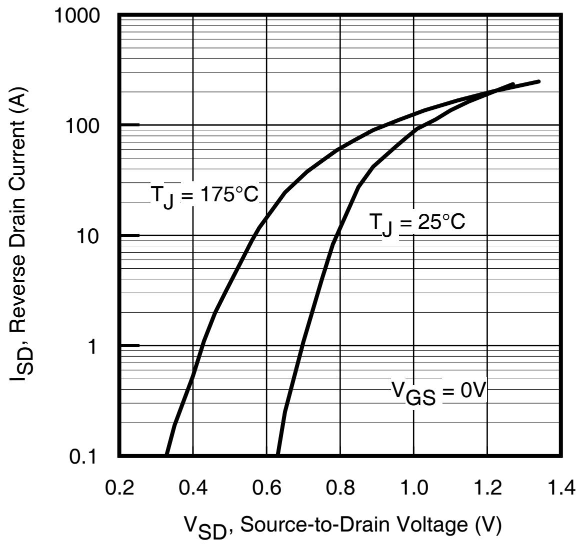


Fig 9. Typical Source-Drain Diode Forward Voltage

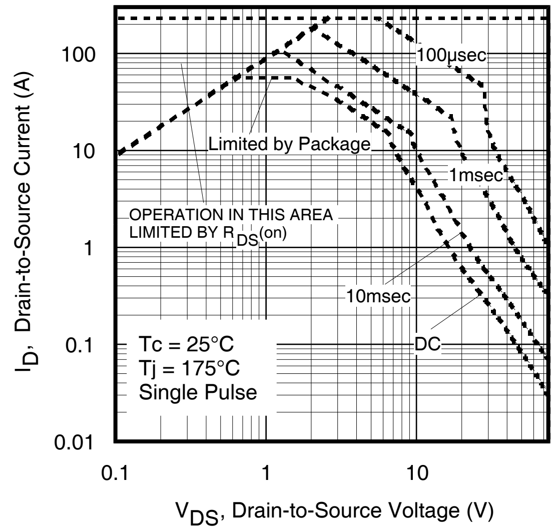


Fig 10. Maximum Safe Operating Area

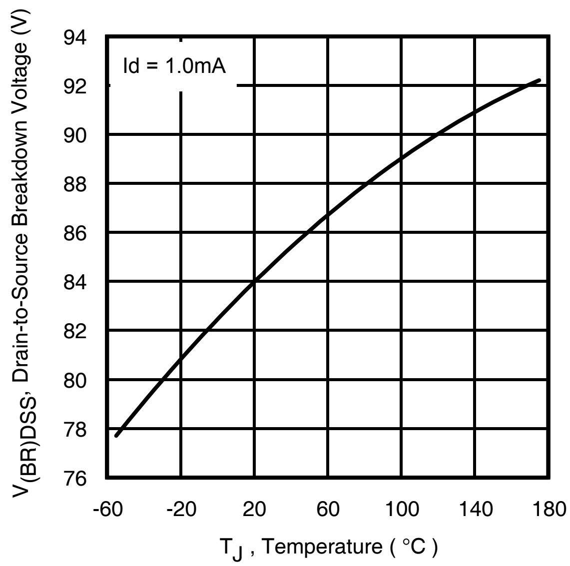


Fig 11. Drain-to-Source Breakdown Voltage

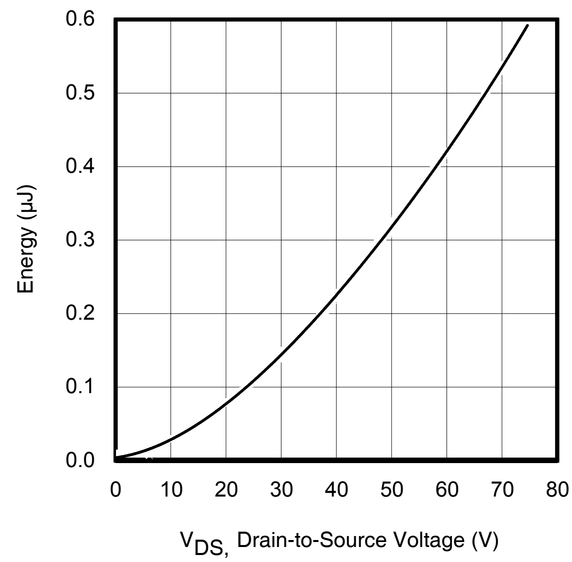


Fig 12. Typical C_{oss} Stored Energy

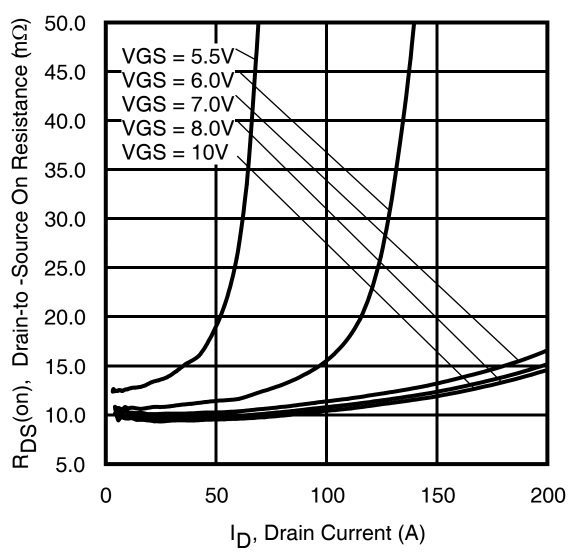


Fig 13. Typical On-Resistance vs. Drain Current

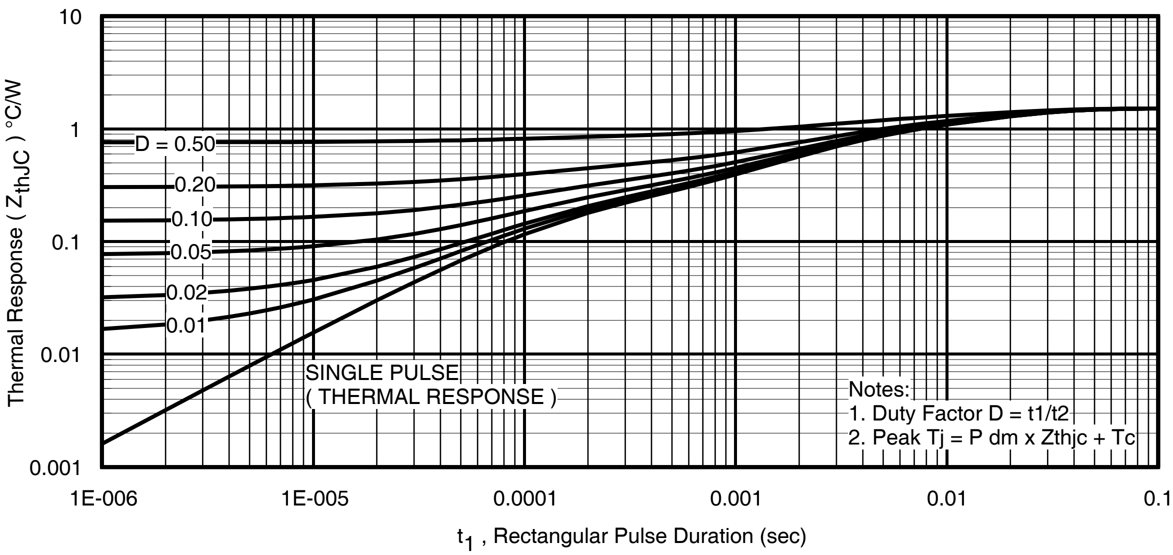


Fig 14. Maximum Effective Transient Thermal Impedance, Junction-to-Case

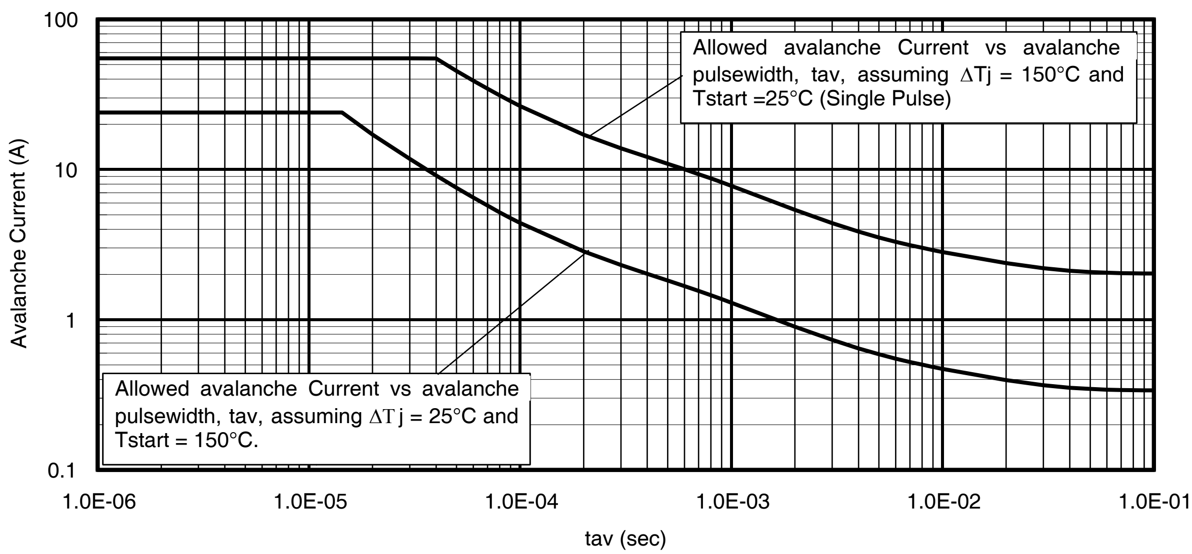


Fig 15. Avalanche Current vs. Pulse Width

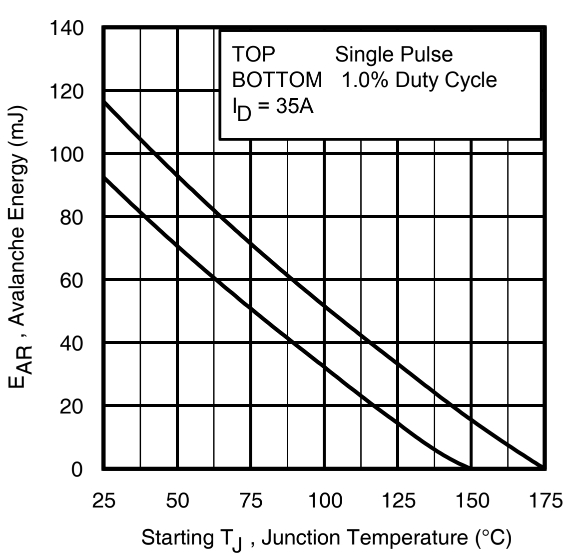


Fig 16. Maximum Avalanche Energy vs. Temperature

Notes on Repetitive Avalanche Curves , Figures 15, 16:
(For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption:
   Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax}. This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 23a, 23b.
4. $P_{D\ (ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 14, 15).
   t_{av} = Average time in avalanche.
   D = Duty cycle in avalanche = tav ·f
   $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13)
   $PD\ (ave) = 1/2\ (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$
   $I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$
   $E_{AS\ (AR)} = P_{D\ (ave)} \cdot t_{av}$

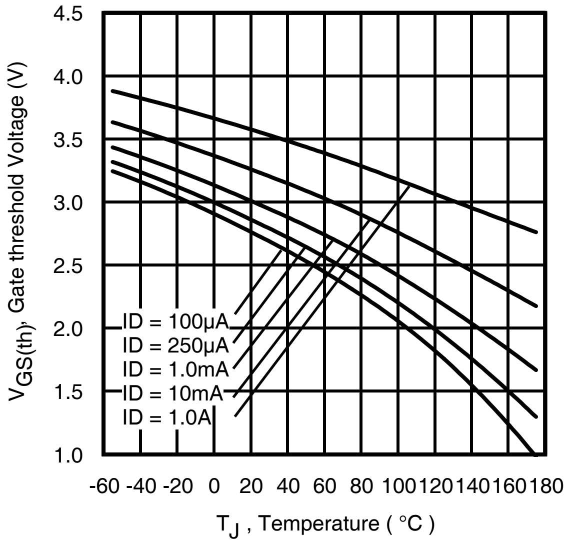


Fig 17. Threshold Voltage vs. Temperature

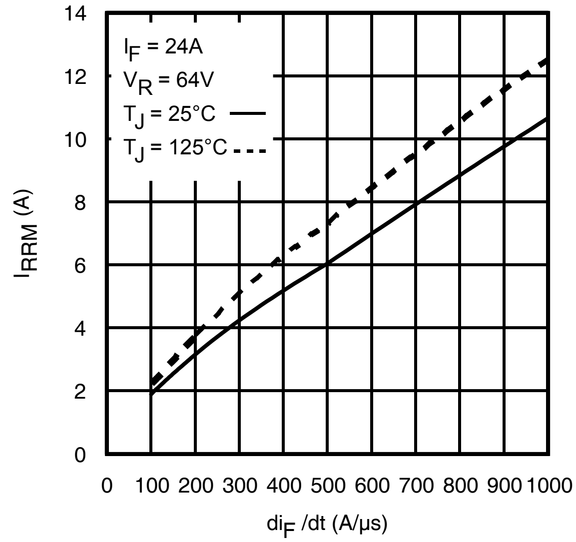


Fig 18. Typical Recovery Current vs. dif/dt

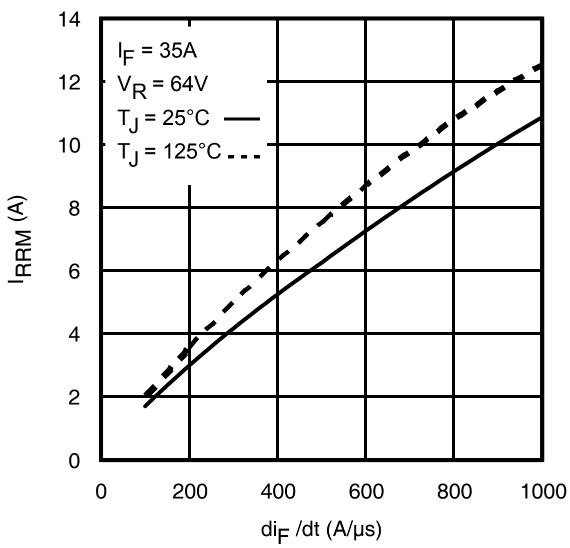


Fig 19. Typical Recovery Current vs. dif/dt

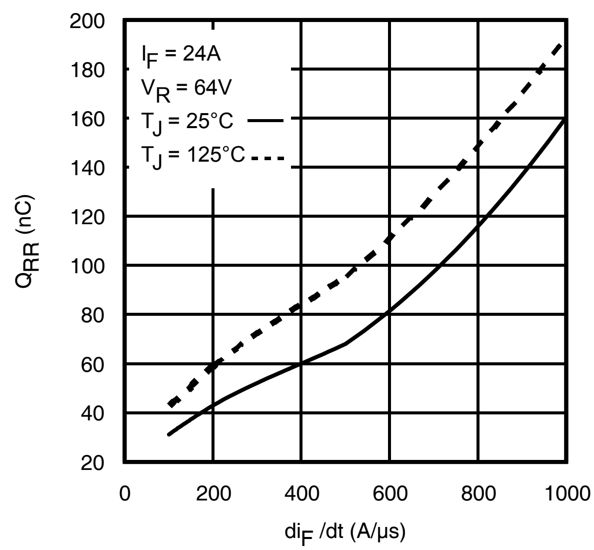


Fig 20. Typical Stored Charge vs. dif/dt

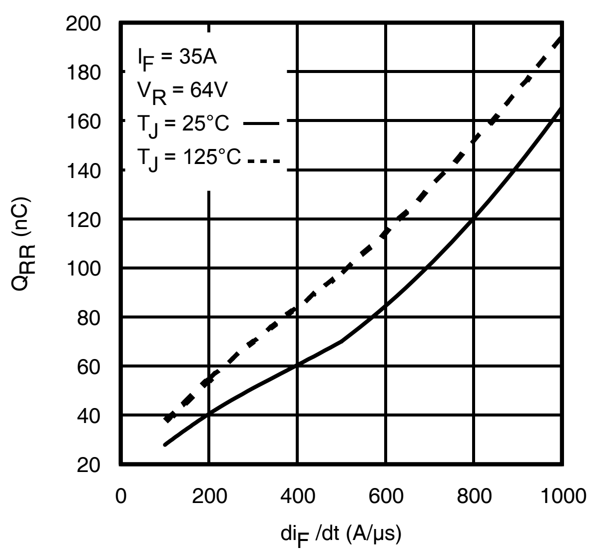


Fig 21. Typical Stored Charge vs. dif/dt

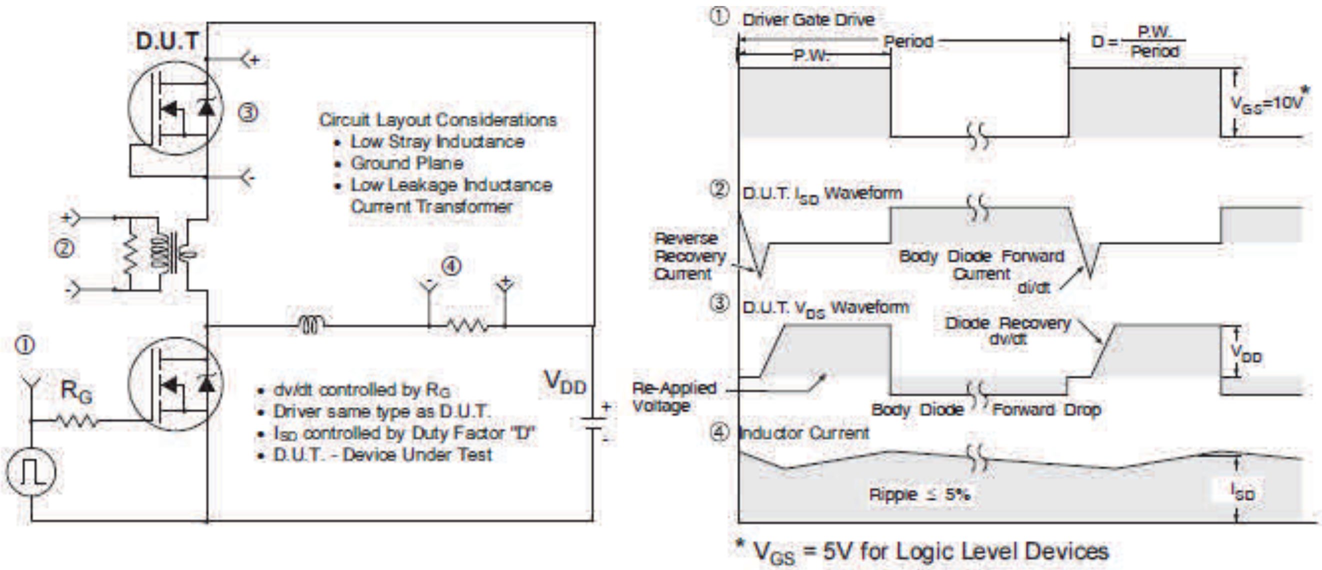


Fig 22. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

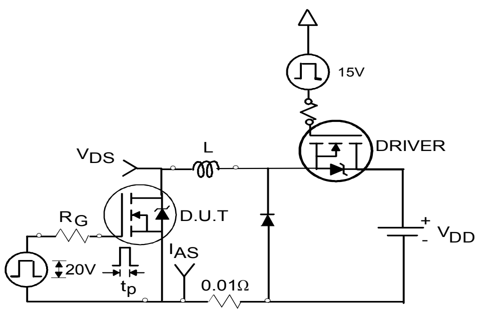


Fig 23a. Unclamped Inductive Test Circuit

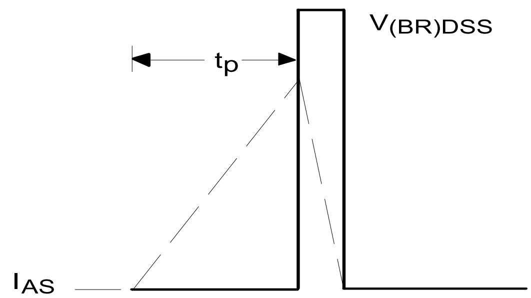


Fig 23b. Unclamped Inductive Waveforms

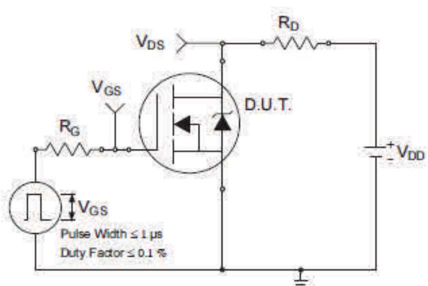


Fig 24a. Switching Time Test Circuit

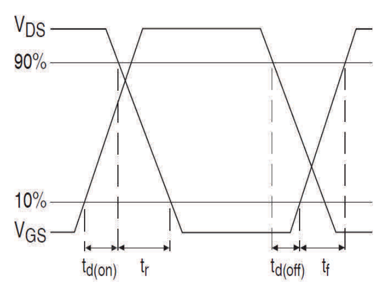


Fig 24b. Switching Time Waveforms

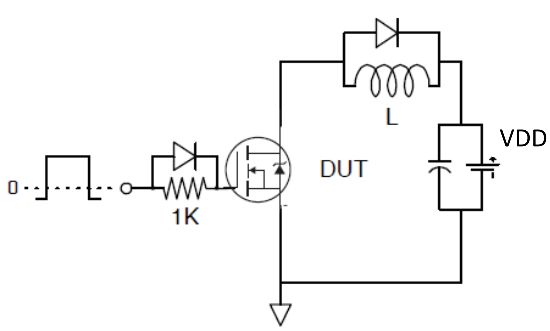


Fig 25a. Gate Charge Test Circuit

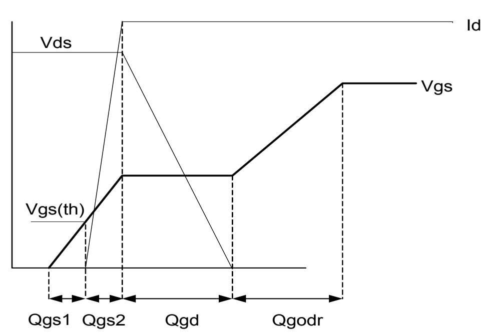
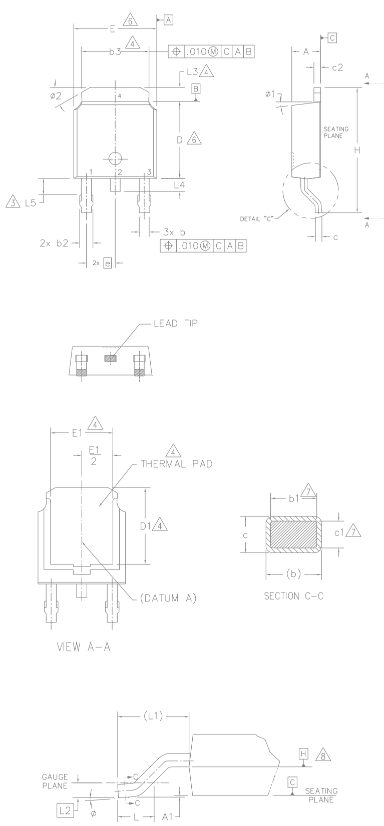


Fig 25b. Gate Charge Waveform

D-Pak (TO-252AA) Package Outline Dimensions are shown in millimeters (inches)



NOTES:

1.– DIMENSIONING AND TOLERANCING PER ASME Y14.5M–1994
2.– DIMENSION ARE SHOWN IN INCHES [MILLIMETERS].
3.– LEAD DIMENSION UNCONTROLLED IN L5.
4.– DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
5.– SECTION C–C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
6.– DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .006 [0.15] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
7.– DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
8.– DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
9.– OUTLINE CONFORMS TO JEDEC OUTLINE TO–252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	–	0.13	–	.005	
b	0.64	0.89	.025	.035	
b1	0.64	0.79	.025	.031	7
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	7
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	6
D1	5.21	–	.205	–	4
E	6.35	6.73	.250	.265	6
E1	4.32	–	.170	–	4
e	2.29 BSC		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 BSC		.108 REF.		
L2	0.51 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	4
L4	–	1.02	–	.040	
L5	1.14	1.52	.045	.060	3
ø	0°	10°	0°	10°	
ø1	0°	15°	0°	15°	
ø2	25°	35°	25°	35°	

LEAD ASSIGNMENTS

HEXFET

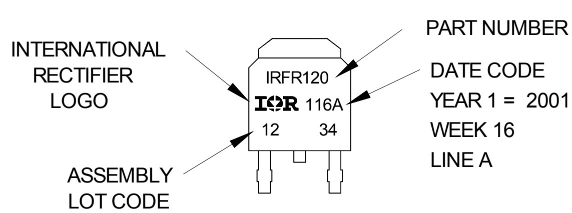
1.– GATE
2.– DRAIN
3.– SOURCE
4.– DRAIN

IGBT & CoPAK

1.– GATE
2.– COLLECTOR
3.– EMITTER
4.– COLLECTOR

D-Pak (TO-252AA) Part Marking Information

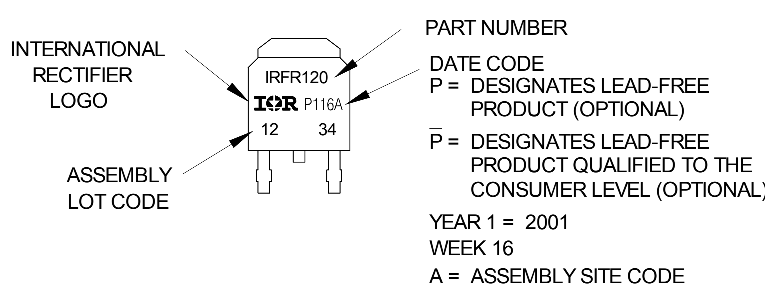
EXAMPLE: THIS IS AN IRFR120
WITH ASSEMBLY
LOT CODE 1234
ASSEMBLED ON WW 16, 2001
IN THE ASSEMBLY LINE "A"



Note: "P" in assembly line position indicates "Lead-Free"

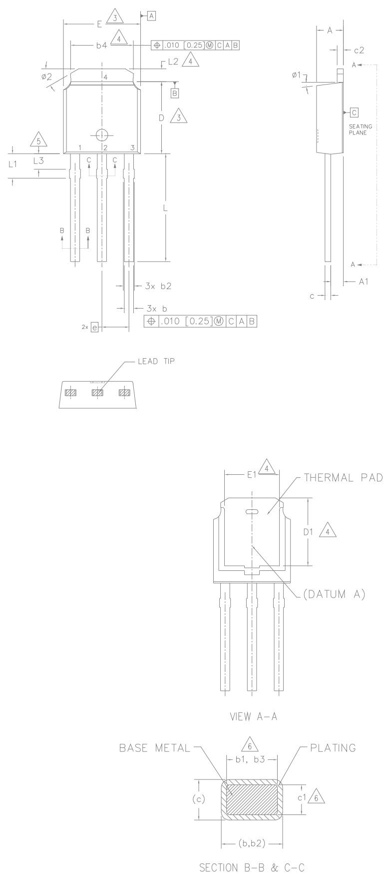
"P" in assembly line position indicates "Lead-Free" qualification to the consumer-level

OR



Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

I-Pak (TO-251AA) Package Outline Dimensions are shown in millimeters (inches)



NOTES:

1.– DIMENSIONING AND TOLERANCING PER ASME Y14.5M–1994

2.– DIMENSION ARE SHOWN IN INCHES [MILLIMETERS].

3.– DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.

4.– THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.

5.– LEAD DIMENSION UNCONTROLLED IN L3.

6.– DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.

7.– OUTLINE CONFORMS TO JEDEC OUTLINE TO–251AA (Date 06/02).

8.– CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	0.89	1.14	.035	.045	
b	0.64	0.89	.025	.035	
b1	0.65	0.79	.025	.031	6
b2	0.76	1.14	.030	.045	
b3	0.76	1.04	.030	.041	6
b4	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	6
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	3
D1	5.21	–	.205	–	4
E	6.35	6.73	.250	.265	3
E1	4.32	–	.170	–	4
e	2.29 BSC		.090 BSC		
L	8.89	9.65	.350	.380	
L1	1.91	2.29	.045	.090	
L2	0.89	1.27	.035	.050	4
L3	0.89	1.52	.035	.060	5
ø1	0°	15°	0°	15°	
ø2	25°	35°	25°	35°	

LEAD ASSIGNMENTS

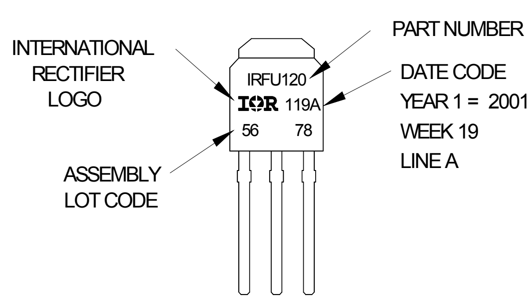
HEXFET

1.– GATE
2.– DRAIN
3.– SOURCE
4.– DRAIN

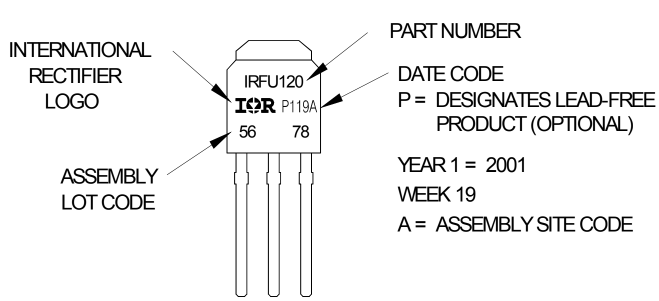
I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120
WITH ASSEMBLY
LOT CODE 5678
ASSEMBLED ON WW 19, 2001
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position indicates Lead-Free"

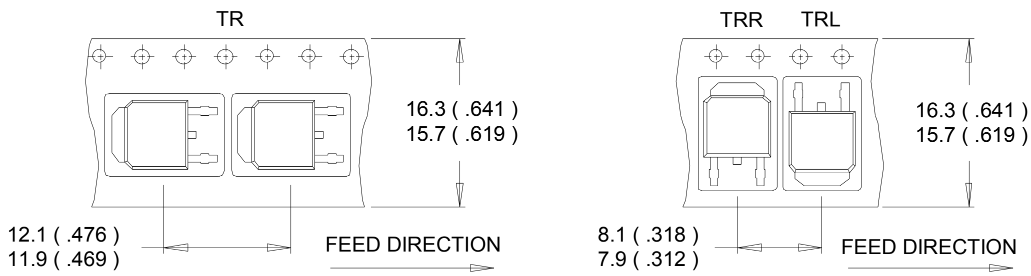


OR

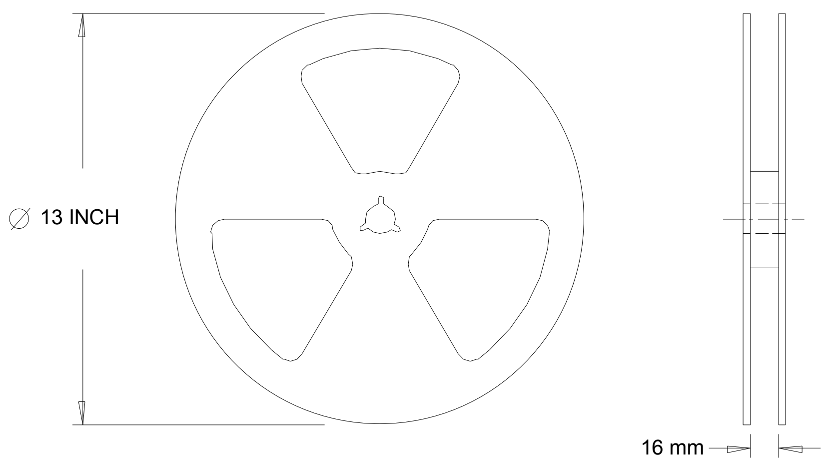


Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

D-Pak (TO-252AA) Tape & Reel Information Dimensions are shown in millimeters (inches)



NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :
1. OUTLINE CONFORMS TO EIA-481.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

Qualification Information†

Qualification Level	Industrial (per JEDEC JESD47F) ††	
Moisture Sensitivity Level	D-Pak	MSL1
	I-Pak	
RoHS Compliant	Yes	

† Qualification standards can be found at International Rectifier's web site: http://www.irf.com/product-info/reliability/

†† Applicable version of JEDEC standard at the time of product release.

Revision History

Date	Comments
11/7/2014	• Updated $E_{AS\ (L=1mH)}$ = 160mJ on page 2 • Updated note 10 "Limited by T_{Jmax}, starting T_J = 25°C, L = 1mH, R_G = 50Ω, I_{AS} = 18A, V_{GS} =10V" on page 2

International
IOR Rectifier

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To contact International Rectifier, please visit http://www.irf.com/whoto-call/

